



General Description

The ZM027N03N combines advanced trench MOSFET technology with a low resistance package to provide extremely low R_DS(ON) . This device is ideal for load switch and battery protection applications.

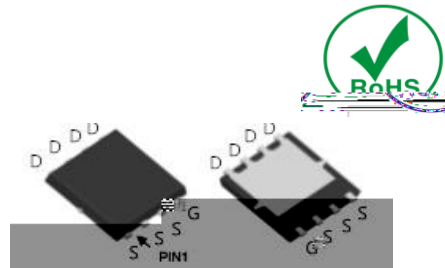
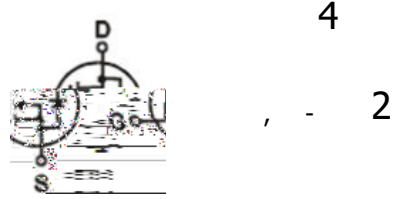
Features

- Advance high cell density Trench technology
R_DS(ON) to minimize conductive loss

Application

nd Synchronous Rectifier

Product Summary



Ordering Information:

Table with 2 columns and 4 rows containing ordering information such as package type (2, 4, 4), reel tape, and quantity (3000).

Absolute Maximum Ratings T_C =25

Table with 4 columns: Parameter, Symbol, Rating, Unit. Lists various electrical ratings like Drain-Source Voltage (30V), Gate-Source Voltage (±20V), and Continuous Drain Current (95A).





Fig.7 Switching Time Measurement Circuit

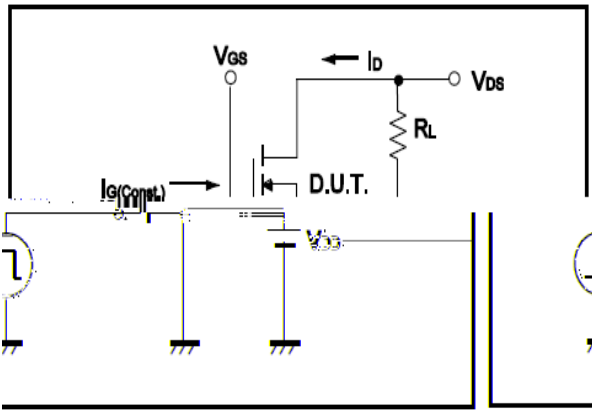


Fig.8 Gate Charge Waveform

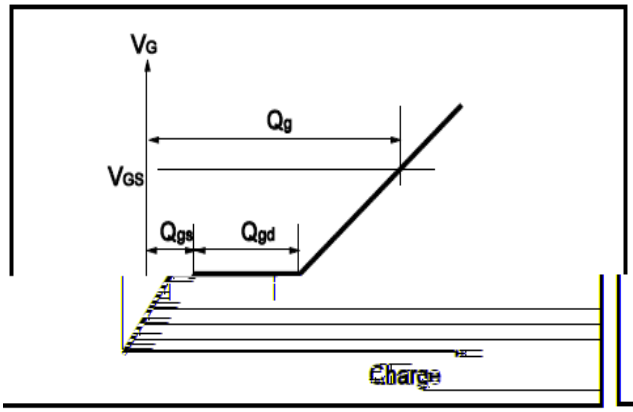


Fig.9 Switching Time Measurement Circuit

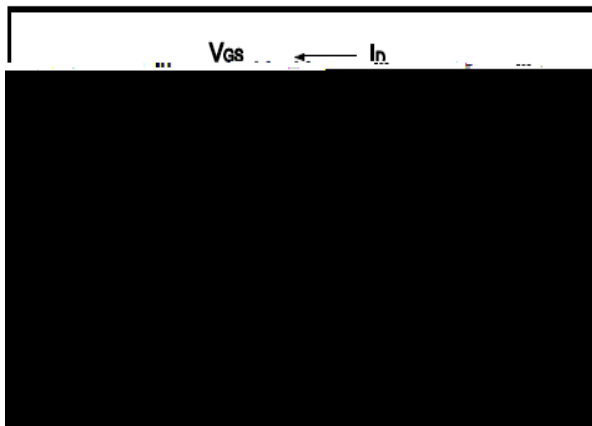


Fig.10 Gate Charge Waveform

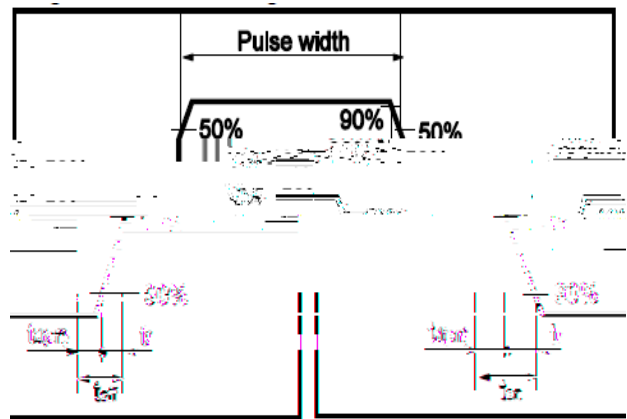


Fig.11 Avalanche Measurement Circuit

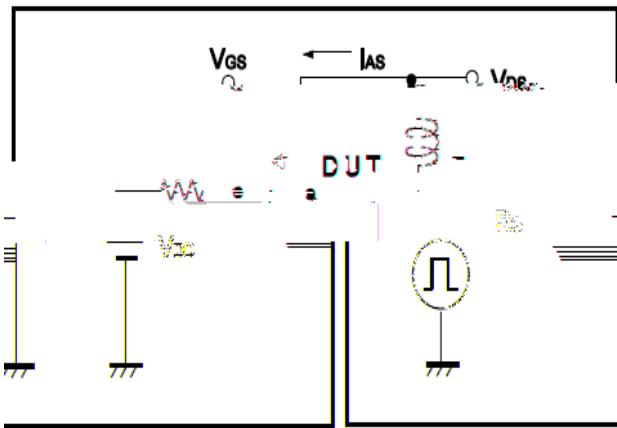
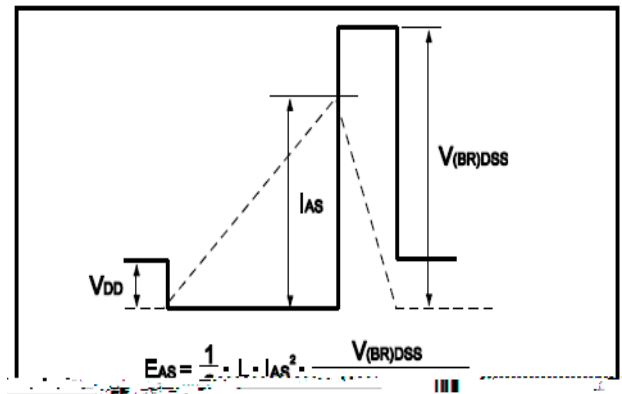


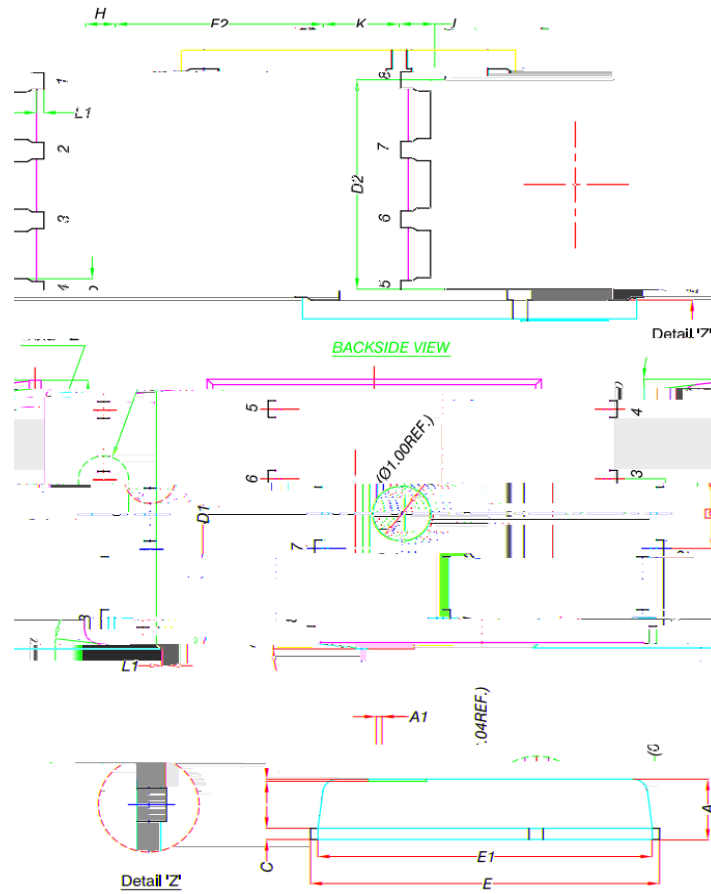
Fig.12 Avalanche Waveform





Dimensions DFN5x6

Unit mm



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0	-	0.05
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96

